



TO-92L Plastic-Encapsulate Transistors

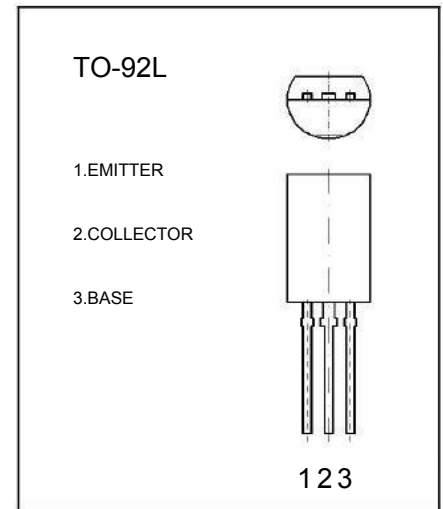
B605 TRANSISTOR(PNP)

FEATURES

Low collector to emitter saturation voltage $V_{CE(sat)}$.
Complementary pair with D571

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter		Units
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-0.7	A
P_C	Collector Power Dissipation	1.0	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100\text{mA}$	90	200	400	
DC current gain	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-500\text{mA}$	50	120		
Transition frequency	f_T	$V_{CE}=-6V, I_C=-500\text{mA}$		-120		MHz

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	90-180	135-270	200-400